

TEMIC

Siliconix

VN0610L, VN10KE/KM, VN2222L

N-Channel Enhancement-Mode MOS Transistors

Zener Gate Protected

Product Summary

Part Number	V _{(BR)DSS} Min (V)	r _{DS(on)} Max (Ω)	V _{GS(th)} (V)	I _D (A)
VN0610L	60	5 @ V _{GS} = 10 V	0.8 to 2.5	0.27
VN10KE		5 @ V _{GS} = 10 V	0.8 to 2.5	0.17
VN10KM		5 @ V _{GS} = 10 V	0.8 to 2.5	0.31
VN2222L		7.5 @ V _{GS} = 10 V	0.6 to 2.5	0.23

Features

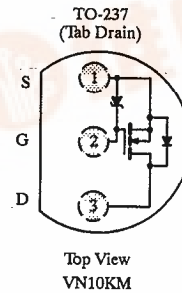
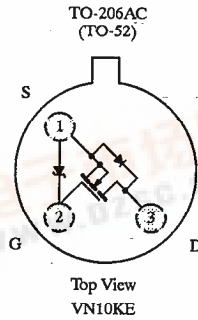
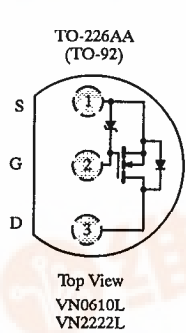
- Zener Diode Input Protected
- Low On-Resistance: 3 Ω
- Ultralow Threshold: 1.2 V
- Low Input Capacitance: 38 pF
- Low Input and Output Leakage

Benefits

- Extra ESD Protection
- Low Offset Voltage
- Low-Voltage Operation
- High-Speed, Easily Driven
- Low Error Voltage

Applications

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays
- Inductive Load Drivers



Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Parameter	Symbol	VN0610L	VN10KE	VN10KM	VN2222L	Unit
Drain-Source Voltage	V _{DS}	60	60	60	60	V
Gate-Source Voltage	V _{GS}	15/-0.3	15/-0.3	15/-0.3	15/-0.3	V
Continuous Drain Current (T _J = 150°C)	I _D	T _A = 25°C	0.27	0.17	0.31	0.23
		T _A = 100°C	0.17	0.11	0.20	0.14
Pulsed Drain Current*	I _{DM}	1	1	1	1	A
Power Dissipation	P _D	T _A = 25°C	0.8	0.3	1	0.8
		T _A = 100°C	0.32	0.12	0.4	0.32
Maximum Junction-to-Ambient	R _{thJA}	156	400	125	156	°C/W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150				°C

Notes

a. Pulse width limited by maximum junction temperature.

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Specifications^a

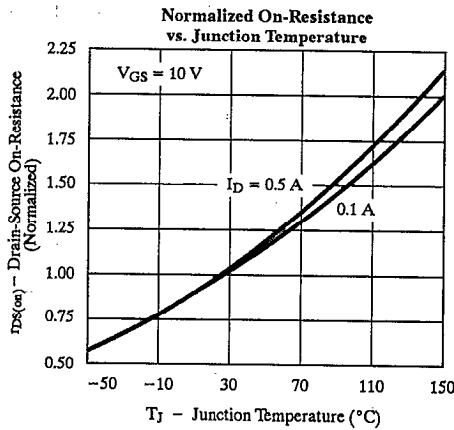
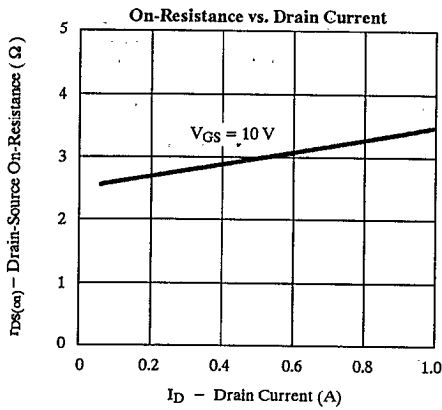
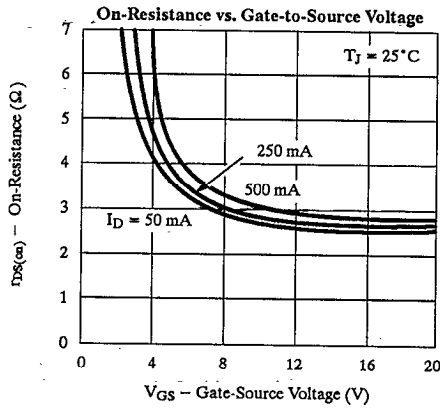
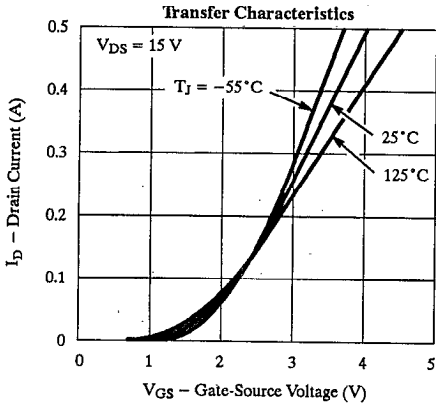
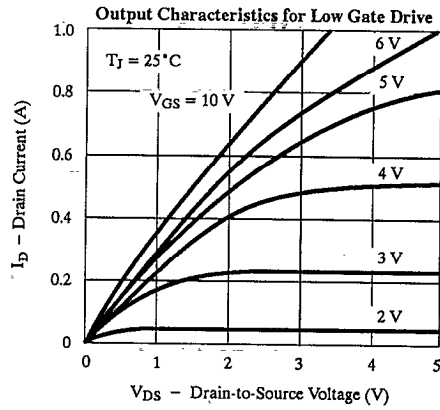
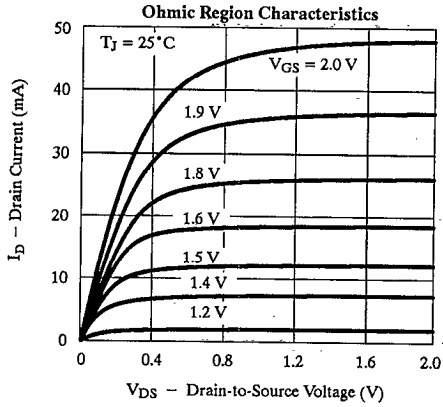
Parameter	Symbol	Test Conditions	Typ ^b	Limits				Unit
				VN0610L VN10KE VN10KM		VN2222L		
				Min	Max	Min	Max	
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	120	60		60		V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\ \text{mA}$	1.2	0.8	2.5	0.6	2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = 15\ \text{V}$	1		100		100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48\ \text{V}, V_{GS} = 0\ \text{V}$ $T_J = 125^\circ\text{C}$			10		10	μA
On-State Drain Current ^c	$I_{D(on)}$	$V_{DS} = 10\ \text{V}, V_{GS} = 10\ \text{V}$	1	0.75		0.75		A
Drain-Source On-Resistance ^c	$r_{DS(on)}$	$V_{GS} = 5\ \text{V}, I_D = 0.2\ \text{A}$	4		7.5		7.5	Ω
		$V_{GS} = 10\ \text{V}, I_D = 0.5\ \text{A}$	3		5		7.5	
		$T_J = 125^\circ\text{C}$	5.6		9		13.5	
Forward Transconductance ^c	g_{fs}	$V_{DS} = 10\ \text{V}, I_D = 0.5\ \text{A}$	300	100		100		mS
Common Source Output Conductance ^c	g_{os}	$V_{DS} = 7.5\ \text{V}, I_D = 0.05\ \text{A}$	0.2					
Dynamic								
Input Capacitance	C_{iss}	$V_{DS} = 25\ \text{V}, V_{GS} = 0\ \text{V}, f = 1\ \text{MHz}$	38		60		60	pF
Output Capacitance	C_{oss}		16		25		25	
Reverse Transfer Capacitance	C_{rss}		2		5		5	
Switching^d								
Turn-On Time	t_{ON}	$V_{DD} = 15\ \text{V}, R_L = 23\ \Omega$ $I_D = 0.6\ \text{A}, V_{GEN} = 10\ \text{V}, R_G = 25\ \Omega$	7		10		10	ns
Turn-Off Time	t_{OFF}		9		10		10	

Notes

- $T_A = 25^\circ\text{C}$ unless otherwise noted.
- For DESIGN AID ONLY, not subject to production testing.
- Pulse test: $PW \leq 300\ \mu\text{s}$ duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.

VNDP06

Typical Characteristics (25°C Unless Otherwise Noted)



Low Power MOS

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Typical Characteristics (25°C Unless Otherwise Noted) (Cont'd)

